

**IN THE SPECIFICATION:**

Please amend the Specification as follows.

Page 1, line 8, after "as" insert --a-- and after "and" (first occurrence) insert --a--.

Page 3, line 20, delete "the"; and

line 22, change "propagates" to --propagate--.

Page 5, line 2, change "An" to --The--;

line 4, change "on a" to --to the--;

line 5, change "of" (second occurrence) to --indicia--;

line 6, delete "a figure of merit" and change "indicates the" to --shows such--;

line 7, after "is" insert --the--;

line 8, delete "the" (second occurrence);

line 9, change "having" to --have--;

line 13, after "of" (second occurrence) insert --the--;

line 14, change "electrode" to --electrode(s)--;

line 17, delete "the", after "with" insert --a-- and after "density"  
insert --of--; and

line 21, change "Thickness" to --Thicknesses--.

Page 9, line 9, delete "change" and after "of" insert --the--;

line 10, after "2" insert --is changed--;

line 13, change "in" to --a-- and after "means" delete ", " (comma);

line 14, after "of" insert --the--;

line 16, delete "the" (first occurrence); and

line 19, after "of" insert --an--.

Page 10, line 13, after "to" insert --the--.

Page 11, line 4, after "such" insert --a--;

line 18, change "Case" to --The case--;

line 22, change "electrode" to --electrode(s)--, delete "the" (second  
occurrence) and delete "a"; and

line 25, after "of" insert --the-- and after "wafer" insert --,--  
(comma).

Page 12, line 1, after "at" insert --a--;

line 5, delete "is";

line 6, change "thick" to --has a thickness--, after "and" delete "in"  
and change "is thin" to --has a thickness--;

line 8, change "was" to --is--; and

line 12, change "Disclosure of the Invention" to --Summary of the  
Invention--.

Page 25, line 5, delete "the" (second occurrence);

line 6, change "figure" to --Figs. 1-3--;

line 11, change "at" to --having the--; and

line 22, after "of" insert --the--.

Page 26, line 5, delete "The";

line 6, change "a" to --the--, after "of" insert --an--, change "the  
connecting" to --connect-- and after "19b" insert --to the upper electrodes 18a  
and 18b--;

line 15, delete "of";

line 17, change "simplified" to --limited to displaying several--, after  
"Since" delete "a" and delete "number of the";

line 19, change "much number of the" to --many--;

line 20, change "from a" to --by-- and change "of the" to --a--;  
line 21, delete "the", change "of" to --a-- and change "does" to --is--;  
line 22, after "not" insert --a-- and after "question" change "a" to  
--of the-- ; and  
line 25, after "wafer," insert --the lower--.

Page 27, line 1, delete "becomes low".

**IN THE CLAIMS:**

Please amend claims 1-6, 8-11, 14 and 15 as follows.

1. (Amended) A film acoustic wave device mounted on a wafer comprising  
[a wafer made of a semiconductor substrate];  
a ground electrode formed on [top of] the [semiconductor substrate]  
wafer;  
a piezoelectric thin film formed on [top of] the ground electrode; and  
[an] at least one upper electrode formed on [top of] the piezoelectric thin  
film, wherein  
a pattern shape [for] of the film acoustic wave device is changed [by]  
according to a position [at] where the film acoustic wave device is mounted on  
the wafer.